Voltage Regulator -Adjustable Output, Positive

LM317L, NCV317L

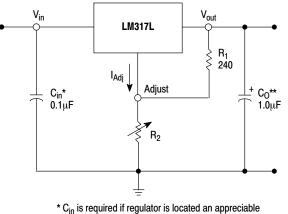
The LM317L is an adjustable 3-terminal positive voltage regulator capable of supplying in excess of 100 mA over an output voltage range of 1.2 V to 37 V. This voltage regulator is exceptionally easy to use and requires only two external resistors to set the output voltage. Further, it employs internal current limiting, thermal shutdown and safe area compensation, making them essentially blow-out proof.

The LM317L serves a wide variety of applications including local, on card regulation. This device can also be used to make a programmable output regulator, or by connecting a fixed resistor between the adjustment and output, the LM317L can be used as a precision current regulator.

Features

- Output Current in Excess of 100 mA
- Output Adjustable Between 1.2 V and 37 V
- Internal Thermal Overload Protection
- Internal Short Circuit Current Limiting
- Output Transistor Safe-Area Compensation
- Floating Operation for High Voltage Applications
- Standard 3–Lead Transistor Package
- Eliminates Stocking Many Fixed Voltages
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb–Free Devices

Simplified Application



 * C_{in} is required if regulator is located an appreciable distance from power supply filter.
** C_O is not needed for stability, however, it does improve transient response.

$$V_{out} = 1.25 V \left(1 + \frac{R_2}{R_1}\right) + I_{Adj} R_2$$

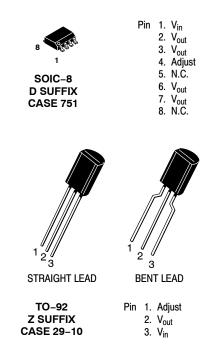
Since I_{Adj} is controlled to less than 100 $\mu A,$ the error associated with this term is negligible in most applications.



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LOW CURRENT THREE-TERMINAL ADJUSTABLE POSITIVE VOLTAGE REGULATOR



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 9 of this data sheet.

DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 9 of this data sheet.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Input-Output Voltage Differential	V _I –V _O	40	Vdc
Power Dissipation Case 29 (TO-92) $T_A = 25^{\circ}C$ Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case	P_D $R_{\theta JA}$ $R_{\theta JC}$	Internally Limited 160 83	W °C/W °C/W
Case 751 (SOIC-8) (Note 1) T _A = 25°C Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case	Ρ _D R _{θJA} R _{θJC}	Internally Limited 180 45	W °C/W °C/W
Maximum Junction Temperature	T _{JMAX}	+150	°C
Storage Temperature Range	T _{stg}	−65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. SOIC-8 Junction-to-Ambient Thermal Resistance is for minimum recommended pad size. Refer to Figure 24 for Thermal Resistance variation versus pad size.

 This device series contains ESD protection and exceeds the following tests: Human Body Model, 2000 V per MIL STD 883, Method 3015. Machine Model Method, 200 V.

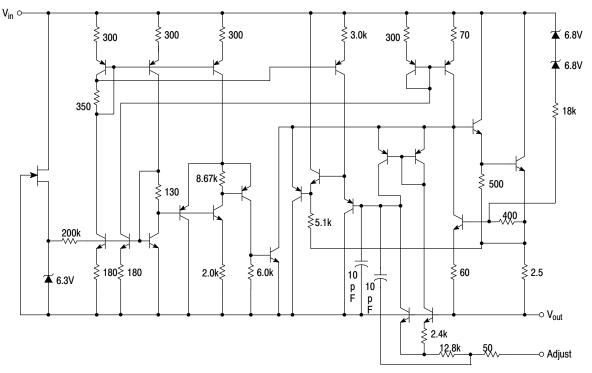


Figure 1. Representative Schematic Diagram

ELECTRICAL CHARACTERISTICS

(VI-VO = 5.0 V; IO = 40 mA; TI = TIOW to Thigh (Note 3); Imax and Pmax (Note 4); unless otherwise noted.)

			LM317L, LB, NCV317LB			
Characteristics	Figure	Symbol	Min	Тур	Мах	Unit
Line Regulation (Note 5) $T_A = 25^{\circ}C, \ 3.0 \ V \leq V_I - V_O \leq 40 \ V$	1	Reg _{line}	-	0.01	0.04	%/V
Load Regulation (Note 5), $T_A = 25^{\circ}C$ 10 mA $\leq I_O \leq I_{max} - LM317L$ $V_O \leq 5.0 V$ $V_O \geq 5.0 V$	2	Reg _{load}	-	5.0 0.1	25 0.5	mV % V _O
Adjustment Pin Current	3	I _{Adj}	-	50	100	μA
$\begin{array}{l} \mbox{Adjustment Pin Current Change} \\ \mbox{2.5 V} \leq V_I - V_O \leq 40 \mbox{ V}, \mbox{ P}_D \leq \mbox{P}_{max} \\ \mbox{10 mA} \leq I_O \leq I_{max} - LM317L \end{array}$	1, 2	ΔI_{Adj}	-	0.2	5.0	μΑ
$ \begin{array}{l} \mbox{Reference Voltage} \\ \mbox{3.0 V} \leq V_I - V_O \leq 40 \mbox{ V}, \mbox{ P}_D \leq \mbox{P}_{max} \\ \mbox{10 mA} \leq I_O \leq I_{max} - LM317L \end{array} $	3	V _{ref}	1.20	1.25	1.30	V
Line Regulation (Note 5), $3.0 \text{ V} \le \text{V}_{\text{I}} - \text{V}_{\text{O}} \le 40 \text{ V}$	1	Reg _{line}	-	0.02	0.07	%/V
Load Regulation (Note 5) 10 mA $\leq I_O \leq I_{max} - LM317L$ $V_O \leq 5.0 V$ $V_O \geq 5.0 V$	2	Reg _{load}	- -	20 0.3	70 1.5	mV % V _O
Temperature Stability $(T_{low} \le T_J \le T_{high})$	3	Τ _S	-	0.7	-	% V _O
Minimum Load Current to Maintain Regulation (V _I – V _O = 40 V)	3	I _{Lmin}	_	3.5	10	mA
$ \begin{array}{l} Maximum \ Output \ Current \\ V_I - V_O \leq 6.25 \ V, \ P_D \leq P_{max}, \ Z \ Package \\ V_I - V_O \leq 40 \ V, \ P_D \leq P_{max}, \ T_A = 25^\circ C, \ Z \ Package \end{array} $	3	I _{max}	100	200 20		mA
RMS Noise, % of V _O T _A = 25°C, 10 Hz \leq f \leq 10 kHz	-	N	-	0.003	-	% V _O
Ripple Rejection (Note 6) $V_O = 1.2 \text{ V}, \text{ f} = 120 \text{ Hz}$ $C_{Adj} = 10 \mu\text{F}, V_O = 10.0 \text{ V}$	4	RR	60 -	80 80		dB
Thermal Shutdown (Note 7)	-	-	-	180	-	°C
Long Term Stability, $T_J = T_{high}$ (Note 8) $T_A = 25^{\circ}C$ for Endpoint Measurements	3	S	-	0.3	1.0	%/1.0 k Hrs.

T_{low} to T_{high} = 0° to +125°C for LM317L -40° to +125°C for LM317LB, NCV317LB
I_{max} = 100 mA P_{max} = 625 mW
Load and line regulation are specified at constant junction temperature. Changes in V_O due to heating effects must be taken into account separately. Pulse testing with low duty cycle is used.
C_{Adj}, when used, is connected between the adjustment pin and ground.
Thermal characteristics are not subject to production test.
Since Long. Term Stability capanet he measured on each device before shipment, this specification is an engineering estimate of average.

8. Since Long-Term Stability cannot be measured on each device before shipment, this specification is an engineering estimate of average stability from lot to lot.

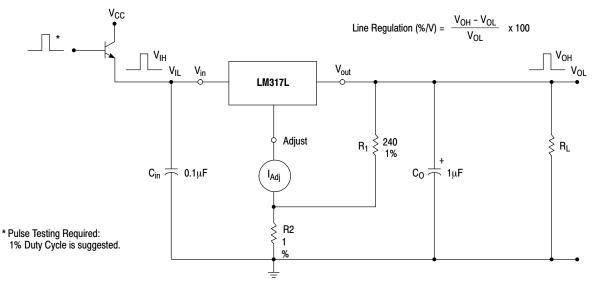


Figure 2. Line Regulation and $\Delta I_{Adj}/Line$ Test Circuit

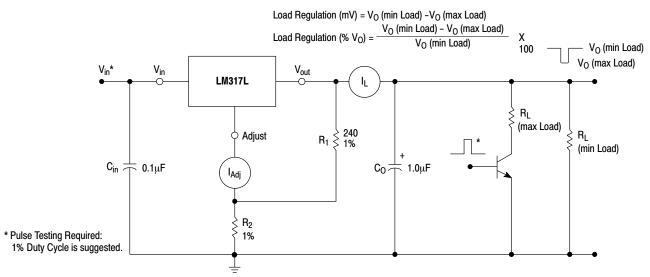
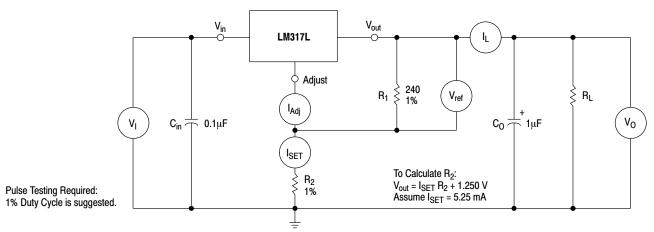
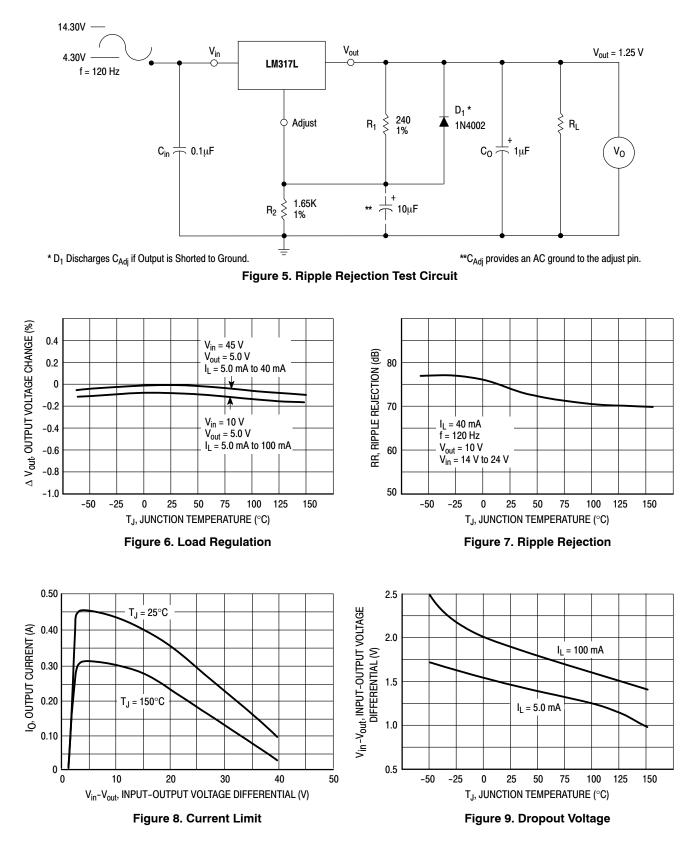
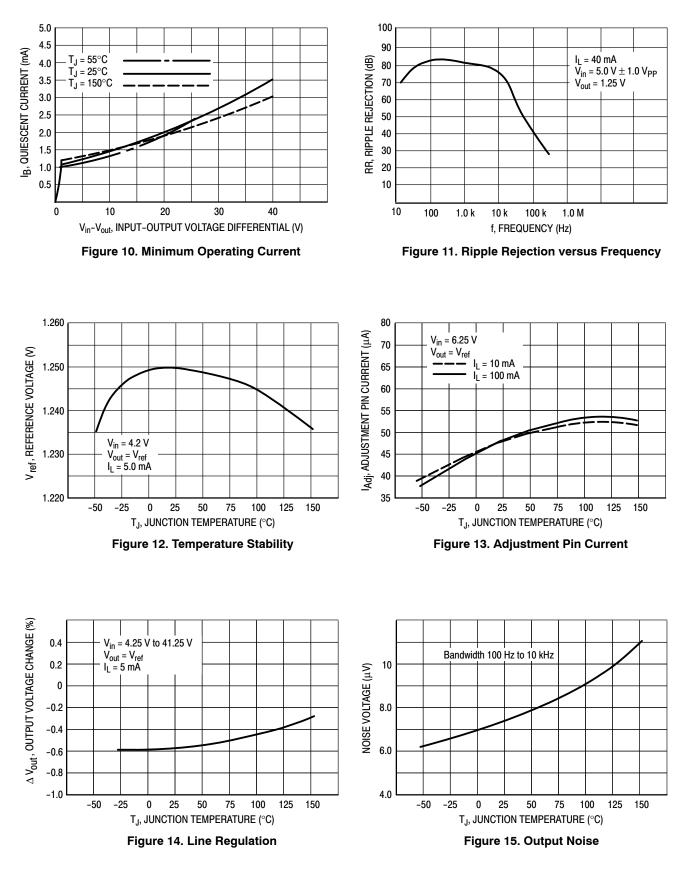


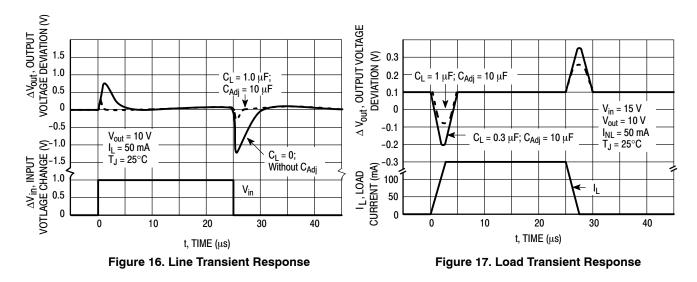
Figure 3. Load Regulation and ΔI_{Adj} /Load Test Circuit











APPLICATIONS INFORMATION

Basic Circuit Operation

The LM317L is a 3-terminal floating regulator. In operation, the LM317L develops and maintains a nominal 1.25 V reference (V_{ref}) between its output and adjustment terminals. This reference voltage is converted to a programming current (I_{PROG}) by R_1 (see Figure 13), and this constant current flows through R_2 to ground. The regulated output voltage is given by:

$$V_{out} = V_{ref} \left(1 + \frac{R_2}{R_1}\right) + I_{Adj} R_2$$

Since the current from the adjustment terminal (I_{Adj}) represents an error term in the equation, the LM317L was designed to control I_{Adj} to less than 100 µA and keep it constant. To do this, all quiescent operating current is returned to the output terminal. This imposes the requirement for a minimum load current. If the load current is less than this minimum, the output voltage will rise.

Since the LM317L is a floating regulator, it is only the voltage differential across the circuit which is important to performance, and operation at high voltages with respect to ground is possible.

V_{in} V_{out} V_{out} Adjust V_{ref} R_1 PROG V_{out} I_{Adj} R_2 V_{ref} = 1.25 V Typical

Figure 18. Basic Circuit Configuration

Load Regulation

The LM317L is capable of providing extremely good load regulation, but a few precautions are needed to obtain maximum performance. For best performance, the programming resistor (R1) should be connected as close to the regulator as possible to minimize line drops which effectively appear in series with the reference, thereby degrading regulation. The ground end of R2 can be returned near the load ground to provide remote ground sensing and improve load regulation.

External Capacitors

A 0.1 μ F disc or 1.0 μ F tantalum input bypass capacitor (C_{in}) is recommended to reduce the sensitivity to input line impedance.

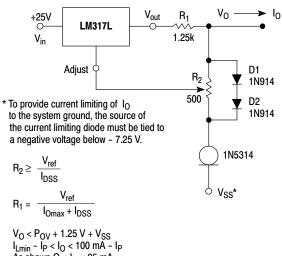
The adjustment terminal may be bypassed to ground to improve ripple rejection. This capacitor (C_{Adj}) prevents ripple from being amplified as the output voltage is increased. A 10 μ F capacitor should improve ripple rejection about 15 dB at 120 Hz in a 10 V application.

Although the LM317L is stable with no output capacitance, like any feedback circuit, certain values of external capacitance can cause excessive ringing. An output capacitance (C_0) in the form of a 1.0 µF tantalum or 25 µF aluminum electrolytic capacitor on the output swamps this effect and insures stability.

Protection Diodes

When external capacitors are used with any IC regulator it is sometimes necessary to add protection diodes to prevent the capacitors from discharging through low current points into the regulator.

Figure 14 shows the LM317L with the recommended protection diodes for output voltages in excess of 25 V or high capacitance values ($C_O > 10 \,\mu\text{F}, C_{Adj} > 5.0 \,\mu\text{F}$). Diode D1 prevents Co from discharging thru the IC during an input short circuit. Diode D2 protects against capacitor CAdi discharging through the IC during an output short circuit. The combination of diodes D_1 and D_2 prevents C_{Adj} from discharging through the IC during an input short circuit.



As shown $O < I_O < 95$ mA

Figure 20. Adjustable Current Limiter

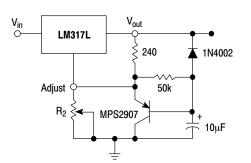


Figure 22. Slow Turn-On Regulator

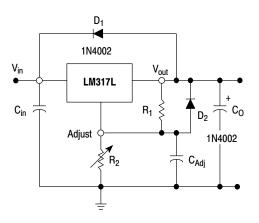
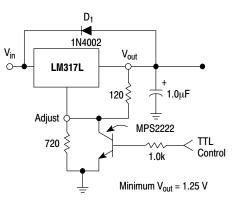


Figure 19. Voltage Regulator with **Protection Diodes**



D₁ protects the device during an input short circuit.

Figure 21. 5.0 V Electronic Shutdown Regulator

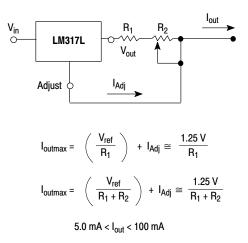
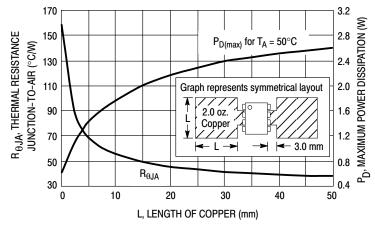
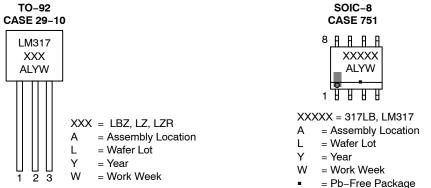


Figure 23. Current Regulator





MARKING DIAGRAMS



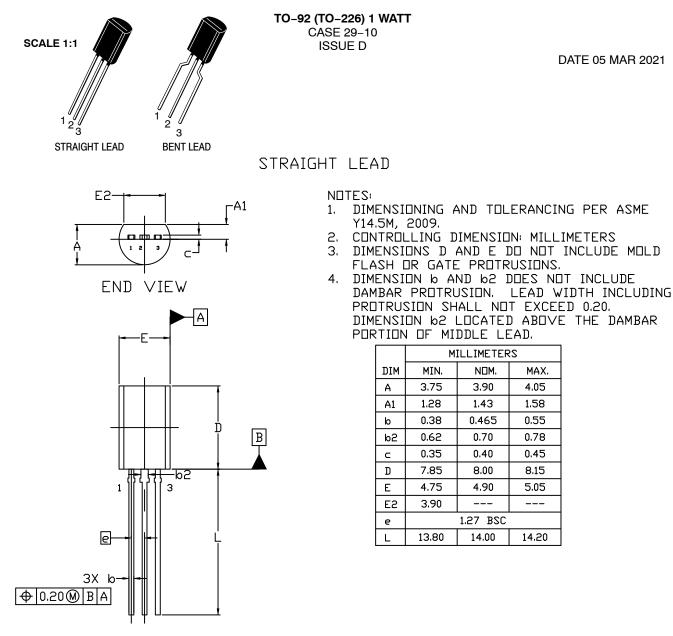
ORDERING INFORMATION

Device	Operating Temperature Range	Package	Shipping [†]
LM317LBDG		SOIC-8 (Pb-Free)	98 Units / Rail
LM317LBDR2G		SOIC-8 (Pb-Free)	2500/Tape & Reel
LM317LBZG		TO-92 (Pb-Free)	2000 Units / Bag
LM317LBZRAG		TO-92 (Pb-Free)	2000 Tape & Reel
LM317LBZRPG	$T_J = -40^{\circ}C \text{ to } +125^{\circ}C$	TO-92 (Pb-Free)	2000 Ammo Pack
NCV317LBDG*		SOIC-8 (Pb-Free)	98 Units / Rail
NCV317LBDR2G*		SOIC-8 (Pb-Free)	2500/Tape & Reel
NCV317LBZG*		TO-92 (Pb-Free)	2000 Units / Bag
NCV317LBZRAG*		TO-92 (Pb-Free)	2000 Tape & Reel
LM317LDG		SOIC-8 (Pb-Free)	98 Units / Rail
LM317LDR2G		SOIC-8 (Pb-Free)	2500/Tape & Reel
LM317LZG		TO-92 (Pb-Free)	2000 Units / Bag
LM317LZRAG	$T_J = 0^{\circ}C$ to $+125^{\circ}C$	TO-92 (Pb-Free)	2000 Tape & Reel
LM317LZREG		TO-92 (Pb-Free)	2000 Tape & Reel
LM317LZRMG		TO-92 (Pb-Free)	2000 Ammo Pack
LM317LZRPG		TO-92 (Pb-Free)	2000 Ammo Pack

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging

Specifications Brochure, BRD8011/D.
*NCV devices: T_{low} = -40°C, T_{high} = +125°C. Guaranteed by design. NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.

<u>Onsemi</u>,



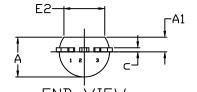
TOP VIEW

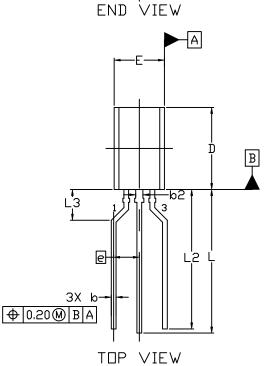
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DATE 05 MAR 2021

FORMED LEAD





NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION b AND b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION b2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS			
DIM	MIN.	NDM.	MAX.	
Α	3.75	3.90	4.05	
A1	1.28	1.43	1.58	
α	0.38	0.465	0.55	
b2	0.62	0.70	0.78	
с	0.35	0.40	0.45	
D	7.85	8.00	8.15	
E	4.75	4.90	5.05	
E5	3.90			
e	2.50 BSC			
L	13.80	14.00	14.20	
L2	13.20	13.60	14.00	
L3	3.00 REF			

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TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

DATE 05 MAR 2021

STYLE 5:

PIN 1. DRAIN

	EMITTER BASE COLLECTOR
	GATE SOURCE & SUBSTRATE DRAIN
2.	ANODE CATHODE & ANODE CATHODE
2.	ANODE GATE CATHODE
2.	COLLECTOR EMITTER BASE
	V _{CC} GROUND 2 OUTPUT

STYLE 2: PIN 1. BASE 2. EMITTER 3. COLLECTOR STYLE 7: PIN 1. SOURCE 2. DRAIN 3. GATE STYLE 12: PIN 1. MAIN TERMINAL 1 2. GATE 3. MAIN TERMINAL 2 STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER STYLE 22: PIN 1. SOURCE 2. GATE 3. DRAIN STYLE 27: PIN 1. MT 2. SUBSTRATE 3. MT STYLE 32 PIN 1. BASE 2. COLLECTOR

3 EMITTER

2.	ANODE ANODE CATHODE
2.	DRAIN Gate Source & Substrate
2.	ANODE 1 GATE CATHODE 2
2.	ANODE CATHODE NOT CONNECTED
2.	GATE SOURCE DRAIN
2.	CATHODE ANODE GATE
2.	: RETURN INPUT OUTPUT

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 9: PIN 1. BASE 1 EMITTER 2. 3. BASE 2 STYLE 14: PIN 1. EMITTER 2. COLLECTOR 3. BASE STYLE 19: PIN 1. GATE 2. ANODE 3. CATHODE STYLE 24: PIN 1. EMITTER 2. COLLECTOR/ANODE 3. CATHODE STYLE 29: PIN 1. NOT CONNECTED 2. ANODE 3. CATHODE

STYLE 34:

PIN 1. INPUT

2. GROUND

3. LOGIC

2. SOURCE 3. GATE STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2 STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE STYLE 35: PIN 1. GATE 2. COLLECTOR 3. EMITTER

GENERIC **MARKING DIAGRAM***

XXXXX XXXXX ALYW= .

XXXX = Specific Device Code

- А = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
 - = Pb-Free Package

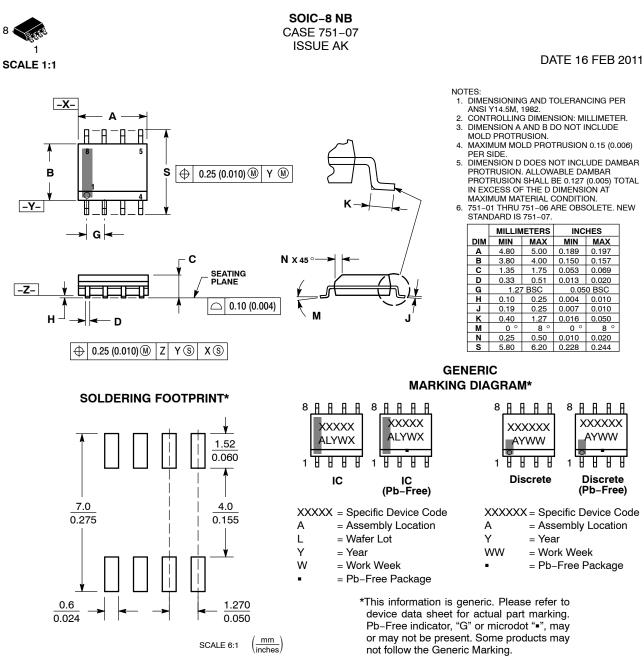
(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN З. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. 8. CATHODE STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE

6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK

7. VOULK 8. VIN

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SOURCE 1/DRAIN 2

7.

8. GATE 1

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7.

8

COLLECTOR, #1

COLLECTOR, #1

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